



74AUP1G17

SINGLE SCHMITT-TRIGGER BUFFER

Description

The Advanced, Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The AUP1G17 is a single, one-input, Schmitt-Trigger buffer gate with a push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using $I_{\rm OFF}$. The $I_{\rm OFF}$ circuitry disables the output preventing damaging current backflow when the device is powered down.

The gate performs the positive Boolean function:

Y = A

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption

 $Icc < 0.9 \mu A$

• Low Dynamic Power Consumption

 $C_{PD} = 6pF$ (Typical at 3.6)

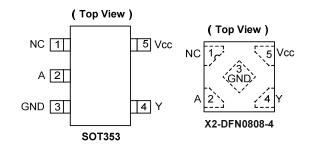
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at Vcc = 3.0V.
- I_{OFF} Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

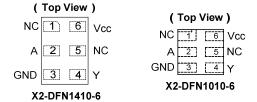
2000-V Human Body Model (A114)

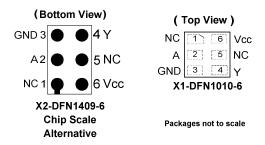
Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments







Applications

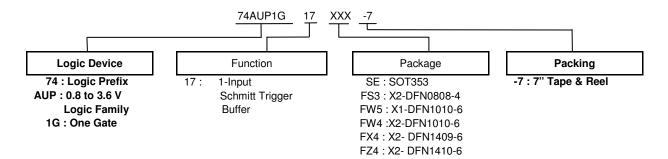
- · Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSDs, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set-Top Boxes

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



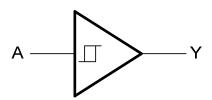
Dovice	Package	Package	Package	7" Tape	and Reel	
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix	
74AUP1G17SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7	
74AUP1G17FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7	
74AUP1G17FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7	
74AUP1G17FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7	
74AUP1G17FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7	
74AUP1G17FZ4-7 FZ4		X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7	

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Pin Descriptions

Pin Name	Function				
NC	No Connection				
Α	Data Input				
GND	Ground				
Y	Data Output				
Vcc	Supply Voltage				

Logic Diagram



Function Table

Inputs	Output				
Α	Υ				
Н	Н				
L	L				

^{5.} The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.



Absolute Maximum Ratings (Notes 6 & 7) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V_{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	50	mA
lok	Output Clamp Current (V _O < 0)	50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	℃
T _{STG}	Storage Temperature	-65 to +150	℃

Notes:

Recommended Operating Conditions (Note 8) (@T_A = +25 ℃, unless otherwise specified.)

Symbol		Parameter	Min	Max	Unit
V _{CC}	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 0.8V	_	-20	μΑ
		V _{CC} = 1.1V	_	-1.1	
	High-Level Output Current	$V_{CC} = 1.4V$	_	-1.7	mA
Іон		V _{CC} = 1.65V	_	-1.9	
		V _{CC} = 2.3V	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		$V_{CC} = 0.8V$	_	20	μΑ
		V _{CC} = 1.1V	_	1.1	
	Lave Lavel Output Current	V _{CC} = 1.4V	_	1.7	ļ
l _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		V _{CC} = 2.3V	_	3.1	
		V _{CC} = 3.0V	_	4	
T _A	Operating Free-Air Temperature		-40	125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{7.} Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

				T _Δ = -	+25℃	T _A = -40℃	C to +85°C	Unit	
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max		
			0.8V	0.4	0.65	0.4	0.65		
			1.1V	0.53	0.9	0.53	0.9		
.,	Positive-Going		1.4V	0.74	1.11	0.74	1.11	.,	
V_{T+}	Input Threshold Voltage	_	1.65V	0.91	1.29	0.91	1.29	V	
	Conago		2.3V	1.37	1.77	1.37	1.77		
			3.0V	1.61	2.32	1.61	2.32		
			V8.0	0.15	0.4	0.15	0.4		
	Negative-Going		1.1V	0.26	0.65	0.26	0.65		
V_{T-}	Input Threshold	_	1.4V	0.39	0.75	0.39	0.75	V	
	Voltage		1.65V	0.47	0.84	0.47	0.84	_	
			2.3V	0.69	1.04	0.69	1.04		
			3.0V	0.88	1.24	0.88	1.24		
			0.8V	0.07	0.5	0.07	0.5		
			1.1V	0.08	0.46	0.08	0.46		
ΔV_T	Hysteresis	_	1.4V	0.18	0.56	0.18	0.56	V	
	$(V_{T+} - V_{T-})$		1.65V	0.27	0.66	0.27	0.66		
			2.3V	0.53	0.92	0.53	0.92		
			3.0V	0.79	1.31	0.79	1.31		
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} - 0.1	_	V _{CC} – 0.1	_		
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.75 x V _{CC}	_	0.7 x V _{CC}	_		
		$I_{OH} = -1.7 \text{mA}$	1.4V	1.11	_	1.03	_	· V	
V _{OH}	High-Level	$I_{OH} = -1.9 \text{mA}$	1.65V	1.32	_	1.30	_		
VOH	Output Voltage	$I_{OH} = -2.3mA$	2.3V	2.05	_	1.97	_		
		I _{OH} = -3.1mA	2.3 V	1.9	_	1.85	_		
		I _{OH} = -2.7mA	0)/	2.72	_	2.67	_		
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_		
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1		
		I _{OL} = 1.1mA	1.1V	_	0.3 x V _{CC}	_	0.3 x V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37		
	Low-Level Output		1.65V	_	0.31	_	0.35	1	
V_{OL}	Voltage	I _{OL} = 2.3mA		_	0.31	_	0.33	V	
		I _{OL} = 3.1mA	2.3V	_	0.44		0.45		
		$I_{OL} = 2.7 \text{mA}$		_	0.31	_	0.33		
		$I_{OL} = 4mA$	3V		0.44		0.45		
l.	Input Current	V _I = GND to 3.6V	0V to 3.6V		± 0.1		± 0.5	11Δ	
l _l	Power Down		0 10 3.00	_		-		μA	
l _{OFF}	Leakage Current	V_I or $V_O = 0V$ to 3.6V	0	_	± 0.2	_	± 0.5	μA	
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 0.2	_	± 0.6	μΑ	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μΑ	
ΔI _{CC}	Additional Supply Current	Input at V _{CC} -0.6V	3.3V	_	40	_	50	μA	



Electrical Characteristics (continued) (@T_A = +25 °C, unless otherwise specified.)

	_			T _Δ = -40 °C	C to +125℃	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Max	
			0.8V	0.4	0.65	
			1.1V	0.53	0.9	_
.,	Positive-Going		1.4V	0.74	1.11	.,
V_{T+}	Input Threshold Voltage	_	1.65V	0.91	1.29	V
	Voltage		2.3V	1.37	1.77	
			3.0V	1.61	2.32	
			0.8V	0.15	0.4	
	Negative-Going		1.1V	0.26	0.65	
V_{T-}	Input Threshold		1.4V	0.39	0.75	V
	Voltage	_	1.65V	0.47	0.84	_ v
			2.3V	0.69	1.04	
			3.0V	0.88	1.24	
			0.8V	0.07	0.5	
			1.1V	0.08	0.46	
ΔV_{T}	Hysteresis	_	1.4V	0.18	0.56	↓ v
ΔVI	$(V_{T+} - V_{T-})$		1.65V	0.27	0.66	<u> </u>
			2.3V	0.53	0.92	
			3.0V	0.79	1.31	
	l F	I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.11	_	
		I _{OH} = -1.1mA	1.1V	0.6 x V _{CC}	_	
		$I_{OH} = -1.7 \text{mA}$	1.4V	0.93	_	
V	High-Level	$I_{OH} = -1.9 \text{mA}$	1.65V	1.17	_	V
V _{OH}	Output Voltage	I _{OH} = -2.3mA	0.01/	1.77	_	V
		I _{OH} = -3.1mA	2.3V	1.67	_	
		I _{OH} = -2.7mA	01/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	_
	Low-Level Output		1.65V	_	0.39	
V_{OL}	Voltage	I _{OL} = 2.3mA		_	0.36	V
		I _{OL} = 3.1mA	2.3V		0.50	
		$I_{OL} = 2.7 \text{mA}$			0.36	_
			3V			
	Innut Current	$I_{OL} = 4mA$	0)/+0.0.0)/	_	0.50	,
l _l	Input Current	$V_I = GND \text{ to } 3.6V$	0V to 3.6V	-	± 0.75	μΑ
loff	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0	_	± 3.5	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μА
ΔI _{CC}	Additional Supply Current	Input at V _{CC} -0.6V	3.3V	_	75	μΑ



Switching Characteristics

C_L=5pF, See Figure 1

Parameter	From Input	TO OUTPUT	V _{CC}	T _A = +25℃			T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
			V CC	Min	Тур	Max	Min	Max	Min	Max	Oilit
			V8.0	_	19.0	_	_	_	_	_	
			1.2V ± 0.1V	2.6	5.7	10.6	2.5	10.9	2.5	11.1	.
	A or B	V	1.5V ± 0.1V	2.4	4.2	6.5	2.3	7.1	2.3	7.4	no
t _{pd}	AUID	ĭ	1.8V ± 0.15V	2.0	3.6	5.5	1.9	6.1	1.9	6.3	ns
			2.5V ± 0.2V	1.9	3.0	4.2	1.8	4.6	1.8	4.8	
			$3.3V \pm 0.3V$	1.5	2.7	3.6	1.5	3.8	1.5	4.0	

C_L=10pF, See Figure 1

Parameter	From Input	To Output	V	T _A = +25℃			T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
			Vcc	Min	Тур	Max	Min	Max	Min	Max	Oilit
			V8.0	_	22.5	_	_	_	_	_	
	A D	Y	1.2V ± 0.1V	2.9	6.6	12.4	2.7	12.9	2.7	13.0	ns
			1.5V ± 0.1V	2.6	4.8	7.8	2.4	8.3	2.4	8.7	
t _{pd}	A or B		1.8V ± 0.15V	2.5	4.2	6.3	2.4	6.8	2.4	7.1	
			$2.5V \pm 0.2V$	2.3	3.5	4.8	2.1	5.3	2.1	5.6	
			$3.3V \pm 0.3V$	1.9	3.3	4.4	1.9	4.6	1.9	4.8	

C_L=15pF, See Figure 1

Parameter	From Input	To Output	V	Т	A = +25°	С	T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
			V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Oill
			V8.0	_	26.0		_		_	1	
		V	1.2V ± 0.1V	3.2	7.4	14.1	3.1	14.7	3.1	14.9	- ns
	A or B		1.5V ± 0.1V	3.1	5.4	8.7	2.8	9.5	2.8	9.9	
t _{pd}	AUID	l '	1.8V ± 0.15V	2.7	4.7	7.1	2.7	7.8	2.7	8.2	
			2.5V ± 0.2V	2.6	4.0	5.6	2.5	6.0	2.5	6.3	
			$3.3V \pm 0.3V$	2.1	3.7	4.9	2.1	5.2	2.1	5.5	

C_L=30pF, See Figure 1

Parameter	From Input	To Output	V	Т	T _A = +25 ℃			T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C	
			Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	36.3	_	-	_	_	_	
		Y	1.2V ± 0.1V	3.9	9.7	19.0	3.7	19.8	3.7	20.1	
	Λ α « D		1.5V ± 0.1V	3.5	7.0	11.2	3.6	12.4	3.6	13.0	
t _{pd}	A or B		1.8V ± 0.15V	3.5	6.0	9.2	3.4	10.1	3.4	10.7	ns
			2.5V ± 0.2V	3.4	5.1	7.0	3.2	7.5	3.2	7.9	
			3.3V ± 0.3V	2.5	4.8	6.2	2.5	7.1	2.5	7.5	



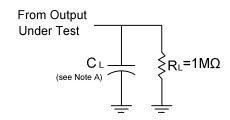
Operating and Package Characteristics (@T_A = +25 ℃, unless otherwise specified.)

	Parameter	Test Conditio	ns	Vcc	Тур	Unit
				V8.0	6.5	
				1.2V ± 0.1V	6.3	
_	Power Dissipation	f = 1MH	lz	1.5V ± 0.1V	6.3	"F
C_{pd}	Capacitance	No Loa	d	1.8V ± 0.15V	6.2	pF
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
Ci	Input Capacitance	$V_i = V_{CC}$ or	GND	0V or 3.3V	1.5	pF
		SOT353			371	
	Thermal Resistance	X2-DFN0808-4	(Note 9)	_	430	
0		X1-DFN1010-6			435	°C/W
θ_{JA}	Junction-to-Ambient	X2-DFN1010-6		_	445	*C/ VV
		X2-DFN1409-6		_	470	
		X2-DFN1410-6		_	460	
		SOT353		_	143	
		X2-DFN0808-4		_	240	
	Thermal Resistance	X1-DFN1010-6	(Note O)	_	250	°C/W
θ_{JC}	Junction-to-Case	X2-DFN1010-6	(Note 9)		250	-G/VV
		X2-DFN1409-6			275	
		X2-DFN1410-6			265	

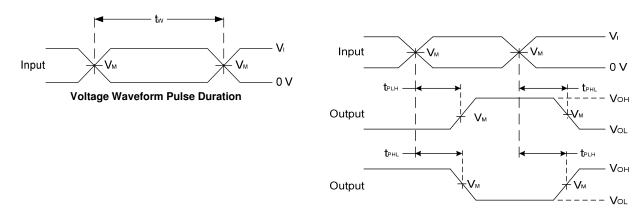
Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Parameter Measurement Information



Vcc	Inputs		V	
VCC	VI	t_r/t_f	V _M	CL
V8.0	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V±0.1V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ±0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V±0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{PD}.



Marking Information

(1) SOT353

(Top View)

XX Y WX

2

3

XX: Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

 \underline{X} : A $^{\sim}$ Z: Internal code

Part Number	Package	Identification Code
74AUP1G17SE-7	SOT353	XT

(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6

(Top View)

XX $\underline{Y}\underline{W}\underline{X}$ XX: Identification Code

Y: Year: 0~9

 $\underline{\underline{W}}$: Week : A~Z : 1~26 week;

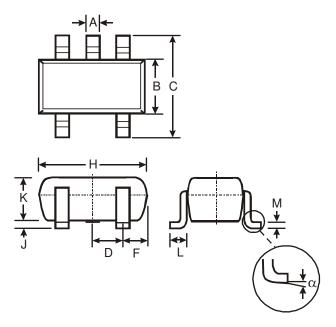
a~z: 27~52 week; z represents 52 and 53 week

X: A~Z: Internal code

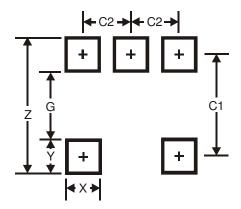
Part Number	Package	Identification Code
74AUP1G17FS3-7	X2-DFN0808-4	YT
74AUP1G17FW5-7	X1-DFN1010-6	QH
74AUP1G17FW4-7	X2-DFN1010-6	XT
74AUP1G17FX4-7	X2-DFN1409-6	HJ
74AUP1G17FZ4-7	X2-DFN1410-6	XT



SOT353 Package Outline Dimensions and Suggested Pad Layout



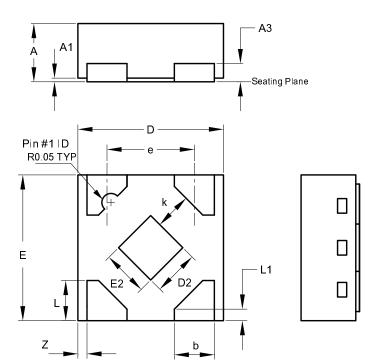
SOT353				
Dim	Min	Max	Тур	
Α	0.10	0.30	0.25	
В	1.15	1.35	1.30	
С	2.00	2.20	2.10	
D		0.65 Typ)	
F	0.40	0.45	0.425	
Н	1.80	2.20	2.15	
J	0	0.10	0.05	
K	0.90	1.00	1.00	
L	0.25	0.40	0.30	
М	0.10	0.22	0.11	
α	0°	8°	-	
All Dimensions in mm				



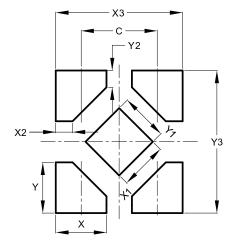
Dimensions	Value (in mm)	
Z	2.5	
G	1.3	
X	0.42	
Υ	0.6	
C1	1.9	
C2	0.65	



X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout



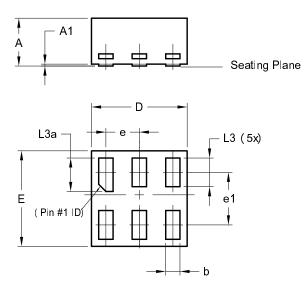
X2-DFN0808-4				
Dim	Min	Max	Тур	
Α	0.25	0.35	0.30	
A1	0	0.04	0.02	
A3	-	-	0.13	
b	0.17	0.27	0.22	
D	0.75	0.85	0.80	
D2	0.15	0.35	0.25	
E	0.75	0.85	0.80	
E2	0.15	0.35	0.25	
е	1	-	0.48	
k	0.20	-	-	
L	0.17	0.27	0.22	
L1	0.02	0.12	0.07	
Z	-	-	0.05	
All Dimensions in mm				



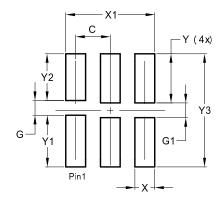
Dimensions	Value
С	0.480
Х	0.320
X1	0.300
X2	0.106
Х3	0.800
Y	0.320
Y1	0.300
Y2	0.106
Y3	0.900



X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout



	X1-DFN1010-6				
	(Iy	pe B)			
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
e 0.35 BSC					
e1		0.55 B	SC		
L3	0.27	0.30	0.30		
L3a	0.32	0.40	0.35		
All Dimensions in mm					

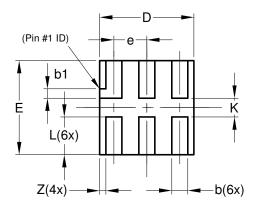


Dimensions	Value	
	(in mm)	
С	0.350	
G	0.150	
G1	0.150	
X	0.200	
X1	0.900	
Υ	0.500	
Y1	0.525	
Y2	0.475	
Y3	1.150	

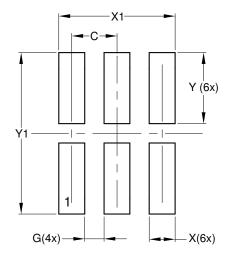


X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





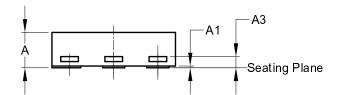
X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A 1	0.00	0.05	0.02	
A3	_	_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_	_	0.35	
L	0.35	0.45	0.40	
K	0.15	_	_	
Z	_	_	0.065	
All Dimensions in mm				

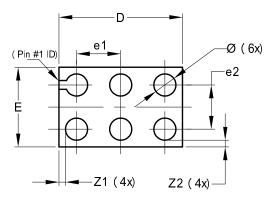


Dimensions	Value (in mm)	
С	0.350	
G	0.150	
Х	0.200	
X1	0.900	
Υ	0.550	
Y1	1.250	

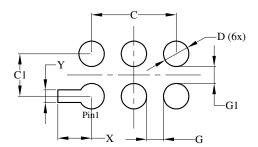


X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout





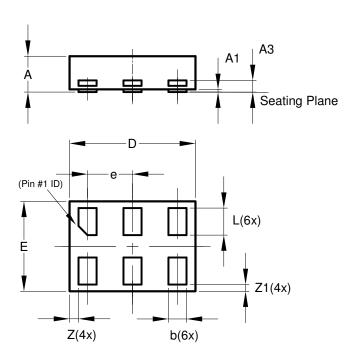
	X2-DFN1409-6				
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	-	-	0.50		
Z 1	-	-	0.075		
Z 2	-	-	0.075		
All Dimensions in mm					



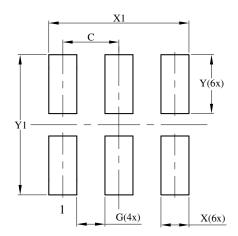
Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400
Υ	0.150



X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6			
Dim	Min	Max	Тур
Α	_	0.40	0.39
A 1	0.00	0.05	0.02
A3			0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
Е	0.95	1.05	1.00
e	_		0.50
L	0.25	0.35	0.30
Z			0.10
Z 1	0.045	0.105	0.075
All Dimensions in mm			



Dimensions	Value	
Difficitisions	(in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Υ	0.525	
Y1	1 250	



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